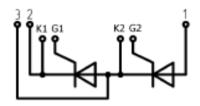
### MSTT/TD740





#### **Key Parameters**

V<sub>DRM</sub> / V<sub>RRM</sub> = 2400 V= 740A $I_{T(AV)}$ = 28000AITSM  $V_{T(TO)}$ = 0.90 V $= 0.21 \text{m}\Omega$ rт

#### **Features**

- Full blocking capability over wide temperature range
- Heat transfer through aluminium oxide ceramic isolated metal baseplate
- Pressure contacts technology for high reliability

### ApplicationsPower Supplies

- DC motor control
- Controlled Rectifiers
- AC switch

#### **Ordering Information**

| MS   | TT   | 740             | K  | ХX  |
|--|--|-----------------|--|---|
| Fixed<br>code  | TT- Thyristor- Thyristor Module<br>TD- Thyristor- Diode Module | Current<br>Code | Technology K = Pressure Contact Technology | Voltage Code<br>Code X 100 = V <sub>DRM</sub> /V <sub>RRM</sub> |
| Order Code MS TT740K24: 2400V VDRM. VRRM. Thyristor-Thyristor Module |  |                 |  |   |

Date of Publication: 25.03.2015 Prepared by : ABA Approved by: RBS Revision

# Technical Information Thyristor / Diode Modules

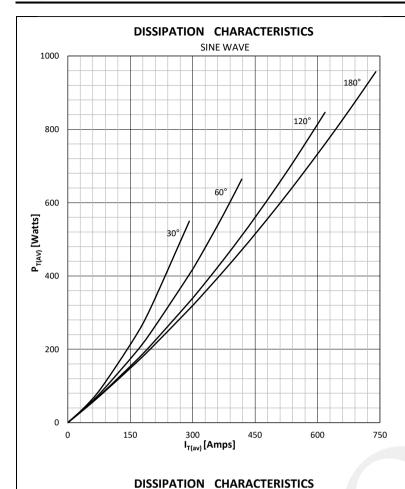
### **MS TT/TD740**

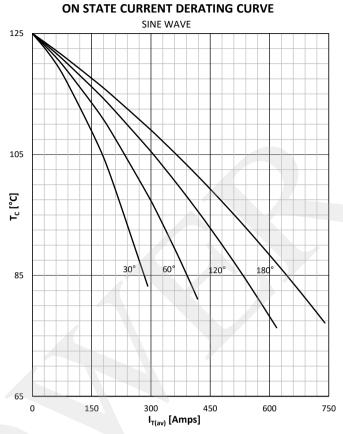


| Symbol            | Characteristic                             | Conditions  | Tj<br>[°C] | Value                  | Unit             |
|-------------------|--|---|------------|------------------------|------------------|
| BLOCKI            | NG   |   |            |                        |                  |
| V RRM             | Repetitive peak reverse voltage            |   | 125        | 2000 - 2400            | V                |
| V RSM             | Non-repetitive peak reverse voltage        |   | 125        | 2100 - 2500            | V                |
| V DRM             | Repetitive peak off-state voltage          |   | 125        | 2000 - 2400            | V                |
| I RRM             | Repetitive peak reverse current            | V= V RRM  | 125        | 150                    | mA               |
| I DRM             | Repetitive peak off-state current          | V= V DRM  | 125        | 150                    | mA               |
| CONDU             | CTING                                      |   | - 11       |                        |                  |
| I T (AV)          | Mean on state current                      | 180° sin ,50 Hz, T <sub>c</sub> =77°C                           |            | 740                    | Α                |
| I RMS             | RMS on-state current                       |   |            | 1162                   | Α                |
|                   |  | Sine wave, 10 ms  | 25         | 28000                  | Α                |
| I TSM             | Surge on-state current                     | Without reverse voltage   | 125        | 24500                  | Α                |
|                   |  | Sine wave, 10 ms  | 25         | 3920 x 10 <sup>3</sup> | A <sup>2</sup> s |
| l² t              | l² t                                       | Without reverse voltage   | 125        | 3001 x 10 <sup>3</sup> | A <sup>2</sup> s |
| V т               | On-state voltage                           | On-state current = 3140A  | 25         | 1.55                   | V                |
| V T(TO)           | Threshold voltage                          |   | 125        | 0.91                   | V                |
| rт                | On-state slope resistance                  |   | 125        | 0.21                   | mΩ               |
| CMITCH            | ·  |   |            |                        |                  |
| SWITCH            | Critical rate of rise of on-state current  | $V_D = 67\%V_{DRM}$ , $I_{TM}=2I_{TAV}$ , Gate pulse $I_G=2A$ , |            |                        |                  |
| di/dt             | non repetitive (f=1Hz)                     | $t_{GP}$ =50µs, $d_{iG}/dt$ ≥1A/µs                              | 125        | 400                    | A/µs             |
| dv/dt             | Critical rate of rise of off-state voltage | $V_{DR} = 67\%V_{DRM}$  | 125        | 1000                   | V/µs             |
| GATE              |  |   |            |                        |                  |
| I gt              | Gate trigger current                       | V <sub>D</sub> =6V  | 25         | 250                    | mA               |
| $V_{gt}$          | Gate trigger voltage                       | V <sub>D</sub> =6V  | 25         | 3.0                    | V                |
| I <sub>H</sub>    | Holding current                            | V <sub>D</sub> =6V, gate open circuit                           | 25         | 300                    | mA               |
| ΙL                | Latching current                           | V <sub>D</sub> =6V  | 25         | 1500                   | mA               |
| MOUNTI            | NG   |   |            | ·                      |                  |
| R th(j-c)         | Thermal impedance, sin 180°                | Junction to case, per arm per module                            |            | 0.050<br>0.025         | °C/W             |
| R th(j-c)         | Thermal impedance, rec120°                 | Junction to case, per arm per module                            |            | 0.0575<br>0.0285       | °C/W             |
| R th(c-h)         | Thermal impedance                          | Case to heatsink, per arm per module                            |            | 0.016<br>0.008         | °C/W             |
| Тj                | Max. junction temperature                  |   |            | 125                    | °C               |
| T stg             | Storage temperature                        |   |            | -40 125                | °C               |
| V <sub>ISOL</sub> | Insulation test voltage,RMS                | F=50Hz, 1min  |            | 3.0                    | KV               |
|                   | Mounting torque                            |   |            | 9 ± 15%                | Nm               |
| M1                |  |   |            | 18 ± 15%               | Nm               |
| M1<br>M2          | Terminal connection torque                 |   |            |                        |                  |

### **MS TT/TD740**







## 

600

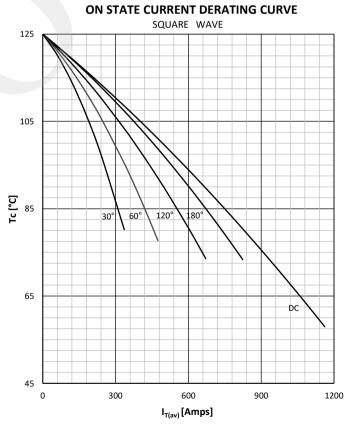
I<sub>T(av)</sub> [Amps]

900

1200

300

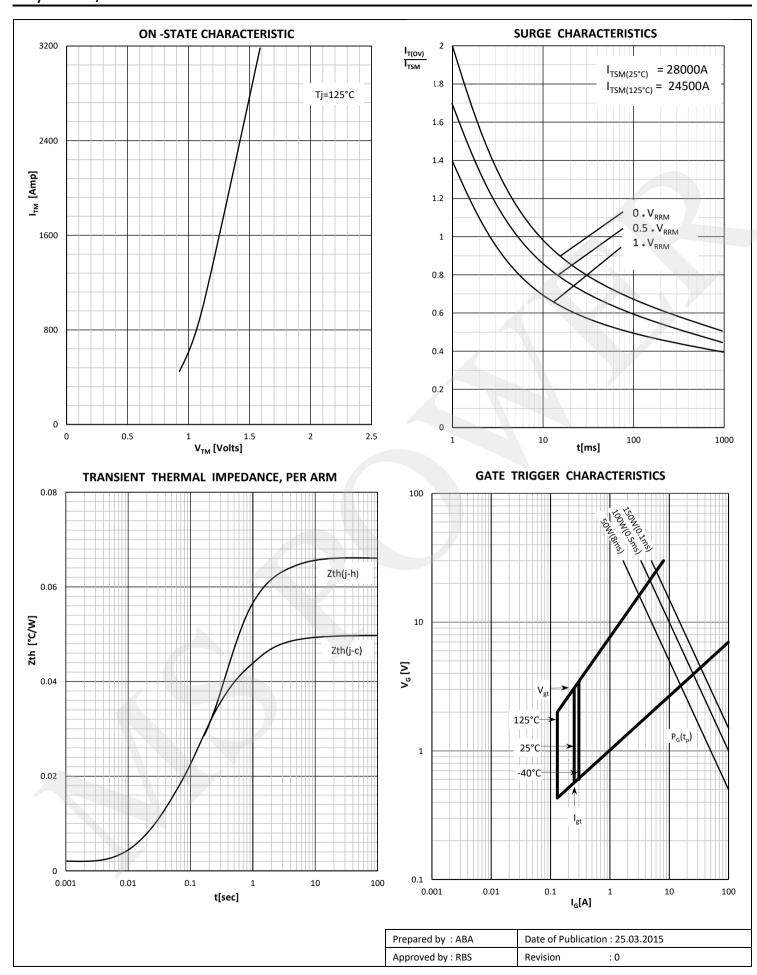
SQUARE WAVE



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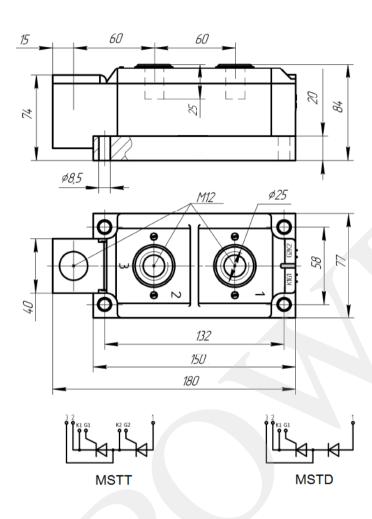




### **MS TT/TD740**



#### **Outline**



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| Prepared by : ABA | Date of Publication | n : 25.03.2015 |
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## Technical Information Thyristor / Diode Modules

### **MS TT/TD740**



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